

#### **Dynamic Power Supply Transmitters**

Learn how envelope tracking, polar modulation, and hybrid designs using these techniques really work. The first physically based and coherent book to bring together a complete overview of such circuit techniques, this is an invaluable resource for practicing engineers, researchers, and graduate students working on RF power amplifiers and transmitters.

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- Step-by-step design guidelines and real-world case studies show you how to put these techniques into practice
- A survey of various transistor technologies will help you to choose which type of transistor to use for best results
- Details on testing and measurement of all aspects of these designs explain how to measure what the circuit is actually doing and how to interpret measurement results

**Earl McCune** is a practicing engineer and Silicon Valley entrepreneur. A graduate of UC Berkeley, Stanford University, and UC Davis, he has over 35 years of post-graduate industry experience in wireless communications circuits and systems and more than 70 issued US patents. Now semi-retired, he has founded two successful start-up companies in addition to working in medium and very large corporations. He is also the author of *Practical Digital Wireless Signals* (Cambridge University Press).



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# Dynamic Power Supply Transmitters

Envelope Tracking, Direct Polar, and Hybrid Combinations

EARL McCUNE





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Dedicated to the outstanding teams I have worked with while learning these details





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## **Preface**

Energy efficiency in all aspects of modern society is now a widespread desire and an active goal. Whether it manifests as driving a high mileage automobile or using a highly rated energy-efficient refrigerator, there is no aspect of modern life that does not benefit from improvement in the energy efficiency used.

Wireless communications are now one of the ubiquitous technological underpinnings of modern society. Mobile communications devices and smart-phones are always at hand and reliably work for the user. As such, it is particularly important for everything involved in wireless communications to be energy efficient. As communication speeds have increased over recent decades, the unfortunate by-product is that the energy efficiency of wireless communications has actually decreased significantly. It is now overdue and important that this gets fixed.

Standards committees have placed the data rate performance of the wireless signals they adopt ahead of any other concern. This means that the energy efficiency of the wireless communication system has not been part of deliberations during the standardization process. The signals adopted years ago are still with us, and there are no plans to change them anytime soon. It is now therefore important to change how these communications devices are made, and to adopt new architectures that will provide the needed energy efficiency while still generating these old signals that are present within the deployed communications standards.

To get full value from this book, the reader should already have a basic familiarity with electrical engineering and wireless communication concepts, including the Fourier transform relationship between time-domain and frequency-domain operations. It is not necessary to have familiarity with the present communications standards.

The contents of this book are drawn from the nearly 20 years of experience I have with dynamic power supply transmitter technology. Being more of a physics-based person than a mathematician, over the decades considerable effort has been given to developing a thorough understanding of the mathematics that underlie the physical relationships being described. Through these pages, I share the results of my efforts with you.

This book is carefully planned so that readers will have a clear understanding of what is being discussed as they work their way through the chapters. This means that the foundations of any topic discussed will as much as possible have already been laid. There are three major parts:



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#### Preface

- principles of the dynamic power supply transmitter techniques,
- circuit implementation and special topics for these designs, and
- new issues for testing and calibration of these designs.

The first two major parts start with the 3-port extensions to linear amplifier operation, and then extend the results first to envelope tracking and then to polar modulation. Hybrid designs that use all of the possible techniques in one product have their own chapter. The extensions needed to explain some unusual results experienced when these techniques are applied at multiple stages in the same transmitter also has its own chapter. Unique contributions in this book include:

- unification of all dynamic power supply operating modes with the inherent characteristics of transistors of any type;
- a specific definition of knee voltage and how this is measured and used;
- direct calculation of what the optimum envelope tracking profile must be for any RF power transistor and selected load line;
- outline of how the concept of matching network design changes significantly when amplifiers are operated in deep compression for polar modulation;
- investigation of the energy efficiency of the various architectures available to implement the dynamic power supply;
- detailed examination of the new interface: connecting the dynamic power supply to the RF PA;
- description of the inherent instabilities in this new interface and what can be done about them;
- clear, unambiguous, and testable definitions of envelope tracking and polar operation, and how these relate to conventional linear operation;
- description of the new transistor specifications needed for polar operation;
- proof that polar operation has higher PA energy efficiency than envelope tracking, and why this must be;
- details of how the concept of amplifier gain must expand into four separate measures that each provide important and different insights;
- identification of the new circuit design rules needed for successful design of polar operation;
- identification of the P-mode amplifier operating region, why this must be avoided by envelope tracking transmitters, and how it can be successfully used by polar operation;
- description of the dynamic power supply feature extensions, including independent automatic compensation at the PA for low battery voltage and/or output impedance mismatch.

Any technology that is involved in multibillion dollar industries, such as wireless communications, is often first published not at a conference or in a technical journal, but rather through the appropriate government patent office. This is certainly true for dynamic power supply transmitter technology. Knowing this fact is particularly important to graduate students who plan on getting doctorate degrees in this technology area, because an idea not seen in the technical journals is not a guarantee that any particular



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idea is really a new contribution to the technical arts. References in the following chapters do include representative patents that are already published, to aid in accessing that library for further searching.

I gratefully acknowledge help with my ability to access transistors and amplifiers using the many semiconductor technologies through the support of Skyworks, Freescale, TriQuint Semiconductor, RF Microdevices, ST Microelectronics, RF Micropower, NXP, Avago Technologies, and Cree. All of these companies have been a huge help in making this story complete. For his particular help, I salute Gray Wong of the RF distributor Richardson RFPD (now Arrow) who tirelessly made good things happen for this project when they needed to.

I want to particularly acknowledge the tremendous help provided by National Instruments, mainly through Haydn Nelson and Takao Inoue, in providing the automated measurement system and software support that allowed me to collect all of the data used for the technology survey in Chapter 10 and in validating the testing requirements presented in Chapter 13. Without this support, the completeness of the technology survey would not have been possible.

The patience of my wife Barbara to the seemingly endless hours spent writing, drawing, rewriting, and editing needed for the preparation of this book is beyond measure. My gratitude to you again is boundless!

I fervently hope that all who read this book, and who may use it as an additional reference, will enjoy the information and approach as much as I have enjoyed writing it.

Earl McCune



## **Abbreviations**

3G Third generation cellular, standardized by the Third Generation

Partnership Project (3GPP)

AC alternating current

ACLR adjacent channel leakage ratio
ACP adjacent channel power

ALBC automatic low battery compensation

AM amplitude modulation

AMO AM offset

AMPR average to minimum power ratio

APT average power tracking  $\beta$  bipolar transistor current ratio BJT bipolar junction transistor

Bluetooth EDR extended data rate mode for Bluetooth<sup>TM</sup>

BPSK binary phase-shift keying

BW bandwidth
BW3 3 dB bandwidth
BWn n dB bandwidth

CCDF complementary cumulative distribution function

CCS controlled current source

CDF cumulative distribution function CDMA code division multiple access

CE constant envelope CFR crest factor reduction

CJTF constant joint transfer function

CMOS complementary metal oxide semiconductor

CoE conservation of energy dBm decibels relative to 1 mW

DC direct current

DC-DC direct current in to direct current out
D-FET depletion mode field effect transistor

DP direct polar

DPS dynamic power supply

DPST dynamic power supply transmitter



List of abbreviations

ххі

DQPSK difference quadrature phase-shift keying DSB-SC double sideband with suppressed carrier

DWC digital wireless communications
EDGE enhanced data rate for GSM evolution

EDR envelope dynamic range

EER envelope elimination and restoration

EF emitter follower

E-FET enhancement mode field effect transistor

EFF envelope flooring and filling ENB equivalent noise bandwith

EpHEMT enhancement mode pseudomorphic high electron mobility

transistor

ET envelope tracking
EVM error vector magnitude
FET field effect transistor
FM frequency modulation
FSK frequency-shift keying
GaAs gallium arsenide
GaN gallium nitride

GMSK Gaussian minimum-shift keying GPRS generalized packet radio service

GSM global system for mobile communications

HBT heterojunction bipolar transistor

HD harmonic distortion

HEMT high electron mobility transistor
HSDPA high-speed downlink packet access

HSPA high-speed packet access

HTOL high temperature operating life test

IMN input matching network
InMN interstage matching network
IQ in-phase/quadrature phase

IV current-voltage

KCL Kirchhoff's Current Law

LDMOS lateral diffused metal oxide semiconductor

LDO low dropout voltage regulator LDVR linear dynamic voltage regulator

LINC linear amplification with nonlinear components

LOS line of sight
LPF lowpass filter
LTE long-term evolution

MESFET metal semiconductor field effect transistor

MOSFET metal oxide semiconductor field effect transistor

NADC North American digital cellular



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NF noise figure
NLOS non line of sight
OBO output back-off

OFDM orthogonal frequency division modulation

OMN output matching network

O-QPSK offset quaternary phase-shift keying

P1dB —1 dB compression point

PA power amplifier

papr peak-to-average-power ratio (linear)
PAPR peak-to-average power ratio (dB)
PCDR power control dynamic range
PDF probability density function
PEP peak envelope power

pHEMT pseudomorphic high electron mobility transistor

PM phase modulation

PMPR peak-to-minimum power ratio

PSD power spectral density
PSR power supply rejection
PSRR power supply rejection ratio
pss power supply sensitivity (linear)
PSS power supply sensitivity (dB)
QAM quadrature amplitude modulation

QM quadrature modulation QPSK quaternary phase-shift keying

R resistance

RBW resolution bandwidth
RC resistor-capacitor
RF radio frequency
rms root-mean-square

RX receiver

SF source follower SiGe silicon germanium

SMPS switch-mode power supply

SR slew rate

SRC spectral raised-cosine SSB single sideband

SSB-SC single sideband with suppressed carrier

SSR stage series resistance
TDM time division multiplex
TETRA terrestrial trunked radio
TRC time raised-cosine
TX transmitter

UMTS universal mobile telephone service



List of abbreviations

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UTB uniform transfer boundary VSWR voltage standing wave ratio

WCDMA wideband code-division multiple access

X reactance Z impedance